

TOSHIBA CMOS DIGITAL INTEGRATED CIRCUIT SILICON MONOLITHIC

**TC74VHCT125AF, TC74VHCT125AFN, TC74VHCT125AFT**  
**TC74VHCT126AF, TC74VHCT126AFN, TC74VHCT126AFT**

**TC74VHCT125AF / AFN / AFT QUAD BUS BUFFER**  
**TC74VHCT126AF / AFN / AFT QUAD BUS BUFFER**

(Note) : The JEDEC SOP (FN) is not available in Japan.

The TC74VHCT125A / 126A are high speed CMOS QUAD BUS BUFFERS fabricated with silicon gate C<sup>2</sup>MOS technology.

They achieve the high speed operation similar to equivalent Bipolar Shottky TTL while maintaining the CMOS low power dissipation.

The TC74VHCT125A requires the 3-state control input  $\bar{G}$  to be set high to place the output into the high impedance state, whereas the TC74VHCT126A requires the control input G to be set low to place the output into high impedance.

The input voltage are compatible with TTL output voltage. This device may be used as a level converter for interfacing 3.3 V to 5 V system.

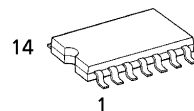
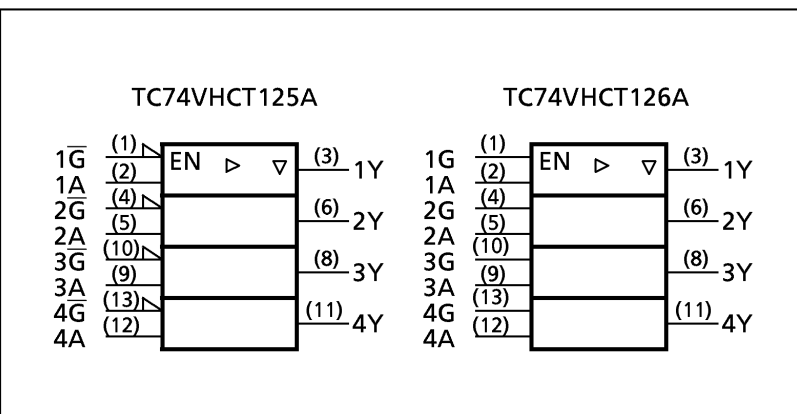
Input protection and output circuit ensure that 0 to 5.5 V can be applied to the input and output\*1 pins without regard to the supply voltage. These structure prevents device destruction due to mismatched supply and input/output voltages such as battery back up, hot board insertion, etc.

\*1:  $V_{CC} = 0 V$

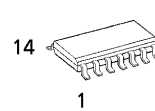
**FEATURES :**

- High Speed.....  $t_{pd} = 3.8 \text{ ns (typ.) at } V_{CC} = 5 V$
- Low Power Dissipation.....  $I_{CC} = 4 \mu A \text{ (Max.) at } T_a = 25^\circ C$
- Compatible with TTL outputs....  $V_{IL} = 0.8 V \text{ (Max.)}$   
 $V_{IH} = 2.0 V \text{ (Min.)}$
- Power Down Protection is provided on all inputs and outputs.
- Balanced Propagation Delays.....  $t_{pLH} \approx t_{pHL}$
- Low Noise .....  $V_{OLP} = 0.8 V \text{ (Max.)}$
- Pin and Function Compatible with the 74 series (74AC / HC / F / ALS / LS etc.) 125 / 126 type.

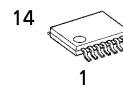
**IEC LOGIC SYMBOL**



F (SOP14-P-300-1.27)  
Weight : 0.18 g (Typ.)

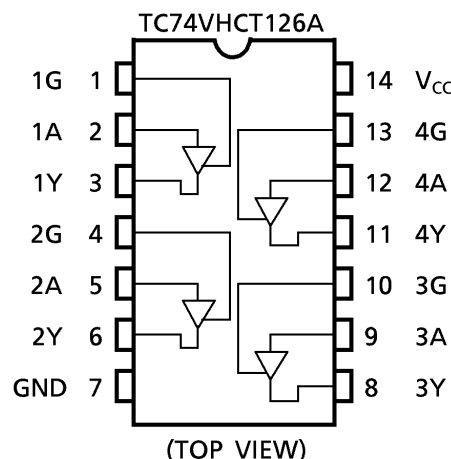
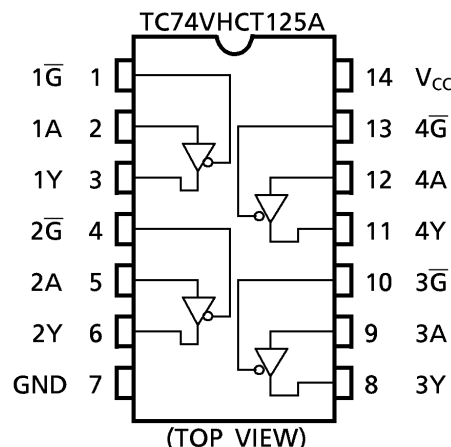


FN (SOL14-P-150-1.27)  
Weight : 0.12 g (Typ.)



FT (TSSOP14-P-0044-0.65)  
Weight : 0.06 g (Typ.)

**PIN ASSIGNMENT**



980910EBA2

● TOSHIBA is continually working to improve the quality and the reliability of its products. Nevertheless, semiconductor devices in general can malfunction or fail due to their inherent electrical sensitivity and vulnerability to physical stress. It is the responsibility of the buyer, when utilizing TOSHIBA products, to observe standards of safety, and to avoid situations in which a malfunction or failure of a TOSHIBA product could cause loss of human life, bodily injury or damage to property. In developing your designs, please ensure that TOSHIBA products are used within specified operating ranges as set forth in the most recent products specifications. Also, please keep in mind the precautions and conditions set forth in the TOSHIBA Semiconductor Reliability Handbook.

## TRUTH TABLE

TC74VHCT125A			TC74VHCT126A		
INPUTS		OUTPUTS	INPUTS		OUTPUTS
$\bar{G}$	A	Y	G	A	Y
H	X	Z	L	X	Z
L	L	L	H	L	L
L	H	H	H	H	H

X: Don't Care  
Z: High Impedance

X: Don't Care  
Z: High Impedance

## ABSOLUTE MAXIMUM RATINGS

PARAMETER	SYMBOL	VALUE	UNIT
Supply Voltage Range	$V_{CC}$	-0.5~7.0	V
DC Input Voltage	$V_{IN}$	-0.5~7.0	V
DC Output Voltage	$V_{OUT}$	-0.5~7.0 (Note 1)	V
		-0.5 ~ $V_{CC} + 0.5$ (Note 2)	
Input Diode Current	$I_{IK}$	-20	mA
Output Diode Current	$I_{OK}$	$\pm 20$ (Note 3)	mA
DC Output Current	$I_{OUT}$	$\pm 25$	mA
DC Vcc/Ground Current	$I_{CC}$	$\pm 50$	mA
Power Dissipation	$P_D$	180	mW
Storage Temperature	$T_{stg}$	-65~150	°C

(Note 1) : Output in Off-State

(Note 2) : High or Low State.  $I_{OUT}$  absolute maximum rating must be observed.(Note 3) :  $V_{OUT} < GND$ ,  $V_{OUT} > V_{CC}$ 

## RECOMMENDED OPERATING CONDITIONS

PARAMETER	SYMBOL	VALUE	UNIT
Supply Voltage	$V_{CC}$	4.5~5.5	V
Input Voltage	$V_{IN}$	0~5.5	V
Output Voltage	$V_{OUT}$	0~5.5 (Note 4)	V
		0~ $V_{CC}$ (Note 5)	
Operating Temperature	$T_{opr}$	-40~85	°C
Input Rise and Fall Time	dt / dV	0~20	ns / V

(Note 4) : Output in Off-State

(Note 5) : High or Low State

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- The information contained herein is subject to change without notice.

## DC ELECTRICAL CHARACTERISTICS

PARAMETER	SYMBOL	CONDITON		Ta = 25°C			Ta = -40~85°C		UNIT	
				V <sub>CC</sub> (V)	MIN.	TYP.	MAX.	MIN.		MAX.
High - Level Input Voltage	V <sub>IH</sub>			4.5~5.5	2.0	—	—	2.0	—	V
Low - Level Input Voltage	V <sub>IL</sub>			4.5~5.5	—	—	0.8	—	0.8	V
High - Level Output Voltage	V <sub>OH</sub>	V <sub>IN</sub> = V <sub>IH</sub> or V <sub>IL</sub>	I <sub>OH</sub> = -50 μA	4.5	4.40	4.50	—	4.40	—	V
			I <sub>OH</sub> = -8 mA	4.5	3.94	—	—	3.80	—	
Low - Level Output Voltage	V <sub>OL</sub>	V <sub>IN</sub> = V <sub>IH</sub> or V <sub>IL</sub>	I <sub>OL</sub> = 50 μA	4.5	—	0.0	0.1	—	0.1	V
			I <sub>OL</sub> = 8 mA	4.5	—	—	0.36	—	0.44	
Input Leakage Current	I <sub>IN</sub>	V <sub>IN</sub> = 5.5 V or GND		0~5.5	—	—	±0.1	—	±1.0	μA
3-State Output Off-state Current	I <sub>OZ</sub>	V <sub>IN</sub> = V <sub>IH</sub> or V <sub>IL</sub> V <sub>OUT</sub> = V <sub>CC</sub> or GND		5.5	—	—	±0.25	—	±2.50	
Quiescent Supply Current	I <sub>CC</sub>	V <sub>IN</sub> = V <sub>CC</sub> or GND		5.5	—	—	4.0	—	40.0	
	I <sub>CCT</sub>	PER INPUT : V <sub>IN</sub> = 3.4 V OTHER INPUT : V <sub>CC</sub> or GND		5.5	—	—	1.35	—	1.50	mA
Output Leakage Current	I <sub>OPD</sub>	V <sub>OUT</sub> = 5.5 V		0	—	—	0.5	—	5.0	μA

**AC ELECTRICAL CHARACTERISTICS (Input  $t_r = t_f = 3$  ns)**

PARAMETER	SYMBOL	TEST CONDITION		Ta = 25°C			Ta = -40~85°C		UNIT	
			V <sub>CC</sub> (V)	CL (pF)	MIN.	TYP.	MAX.	MIN.		MAX.
Propagation Delay Time	t <sub>pLH</sub>		5.0 ± 0.5	15	—	3.8	5.5	1.0	6.5	ns
	t <sub>pHL</sub>			50	—	5.3	7.5	1.0	8.5	
Output Enable Time	t <sub>pZL</sub>	RL = 1 kΩ	5.0 ± 0.5	15	—	3.6	5.1	1.0	6.0	
	t <sub>pZH</sub>			50	—	5.1	7.1	1.0	8.0	
Output Disable Time	t <sub>pZL</sub>	RL = 1 kΩ	5.0 ± 0.5	50	—	6.1	8.8	1.0	10.0	
	t <sub>pZH</sub>									
Output to Output Skew	t <sub>osLH</sub> t <sub>osHL</sub>	(Note 6)	5.0 ± 0.5	50	—	—	1.0	—	1.0	
Input Capacitance	C <sub>IN</sub>				—	4	10	—	10	pF
Output Capacitance	C <sub>OUT</sub>				—	6	—	—	—	
Power Dissipation Capacitance (Note 7)	C <sub>PD</sub>	TC74VHCT125A			—	14	—	—	—	
		TC74VHCT126A			—	15	—	—	—	

(Note 6) : Parameter guaranteed by design.  $t_{osLH} = |t_{pLHm} - t_{pLHn}|$ ,  $t_{osHL} = |t_{pHLm} - t_{pHLn}|$

(Note 7) : C<sub>PD</sub> is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load.

Average operating current can be obtained by the equation :

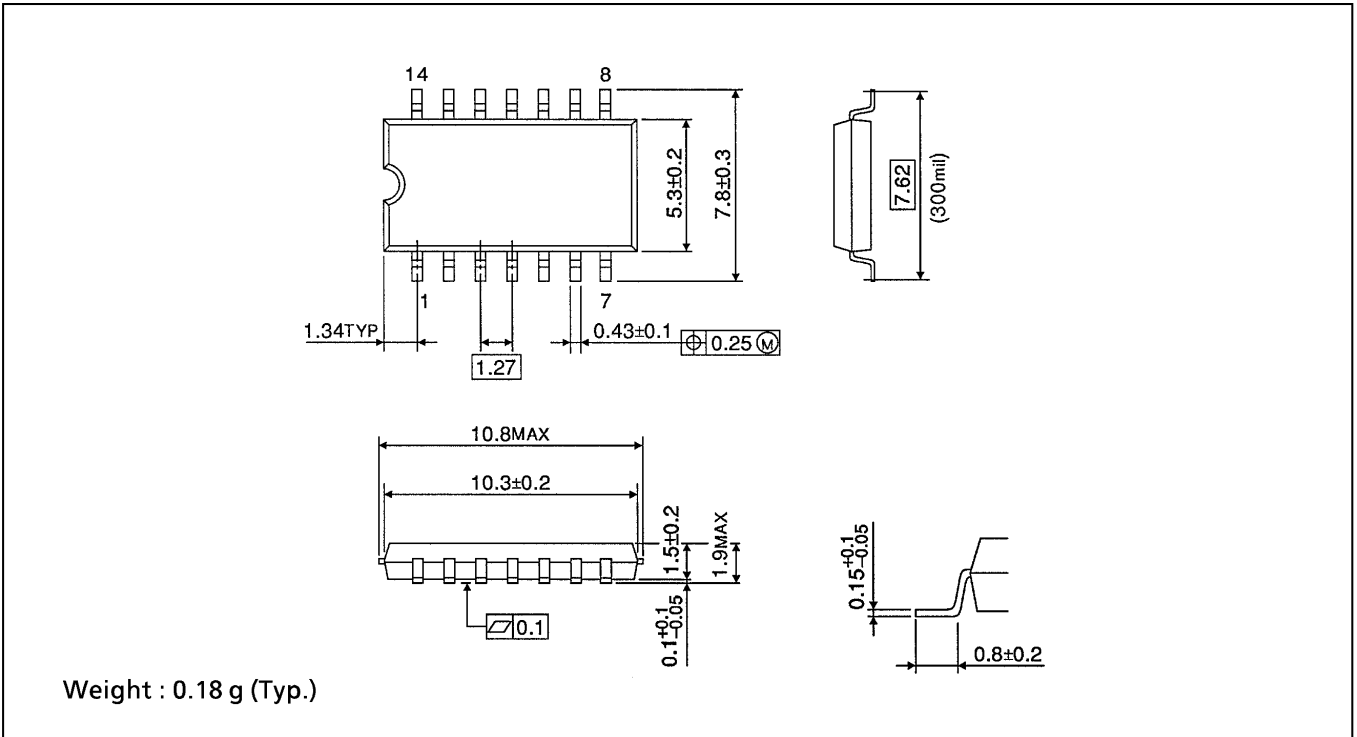
$$I_{CC(opr.)} = C_{PD} \cdot V_{CC} \cdot f_{IN} + I_{CC}/6 \text{ (per Gate)}$$

**NOISE CHARACTERISTICS (Input  $t_r = t_f = 3$  ns)**

PARAMETER	SYMBOL	TEST CONDITION		Ta = 25°C		UNIT
			V <sub>CC</sub> (V)	TYP.	LIMIT	
Quiet Output Maximum Dynamic V <sub>OL</sub>	V <sub>OLP</sub>	C <sub>L</sub> = 50 pF	5.0	0.5	0.8	V
Quiet Output Minimum Dynamic V <sub>OL</sub>	V <sub>OLV</sub>	C <sub>L</sub> = 50 pF	5.0	-0.5	-0.8	V
Minimum High Level Dynamic Input Voltage	V <sub>IHD</sub>	C <sub>L</sub> = 50 pF	5.0	—	2.0	V
Maximum Low Level Dynamic Input Voltage	V <sub>ILD</sub>	C <sub>L</sub> = 50 pF	5.0	—	0.8	V

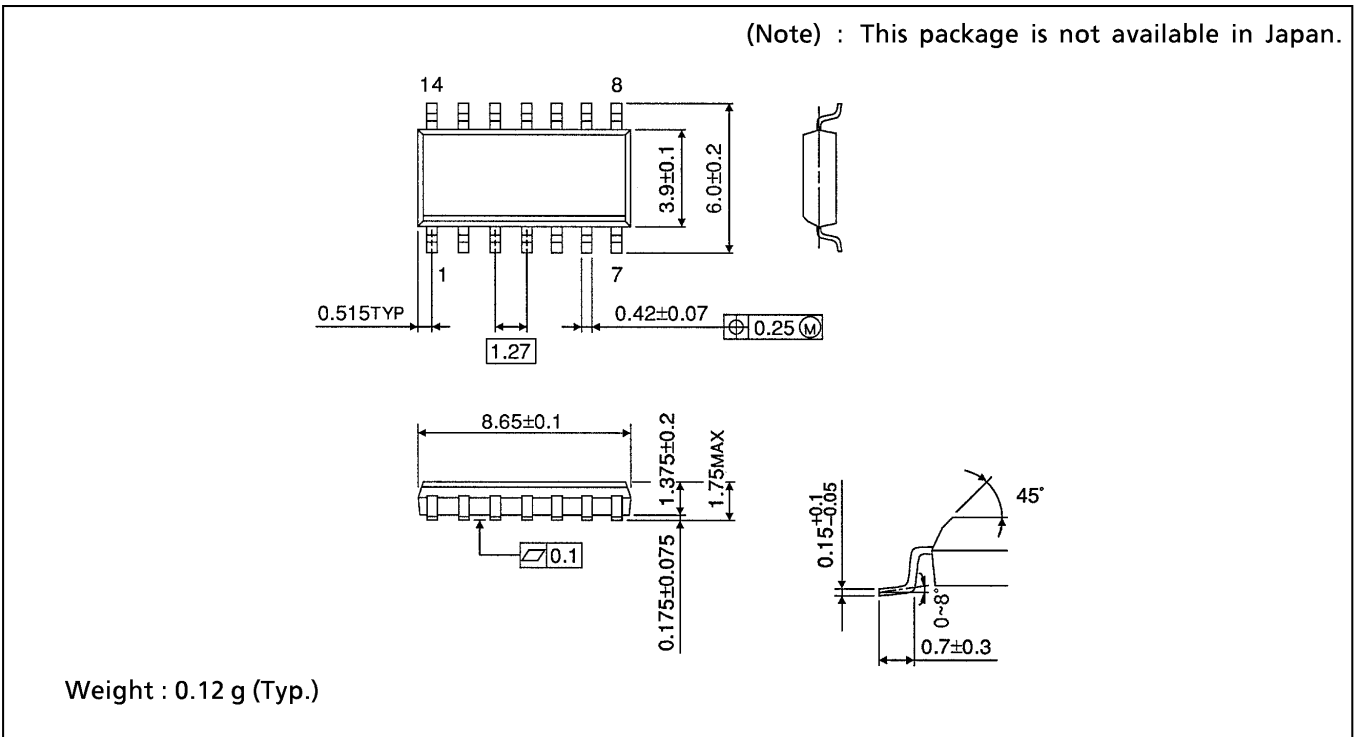
**SOP 14 PIN (200 mil BODY) OUTLINE DRAWING (SOP14-P-300-1.27)**

Unit in mm



**SOP 14 PIN (150 mil BODY) OUTLINE DRAWING (SOP14-P-150-1.27)**

Unit in mm



**TSSOP 14 PIN OUTLINE DRAWING (TSSOP14-P-0044-0.65)**

Unit in mm

